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**SGPT5035** 

# **Technical Data Sheet**

**SGPT5035 5mm Phototransistor** 

#### Descriptions

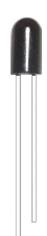
SGPT5035 is a high speed and high sensitive NPN silicon phototransistor molded in a brimless 5 mm package. Due to its black epoxy the device is sensitive to infrared radiation.

#### Features

- Fast response time
- High photo sensitivity
- Pb Free
- The product itself will remain within RoHS compliant version.

### Applications

- Infrared applied system
- Camera
- Printer
- Cockroach catcher



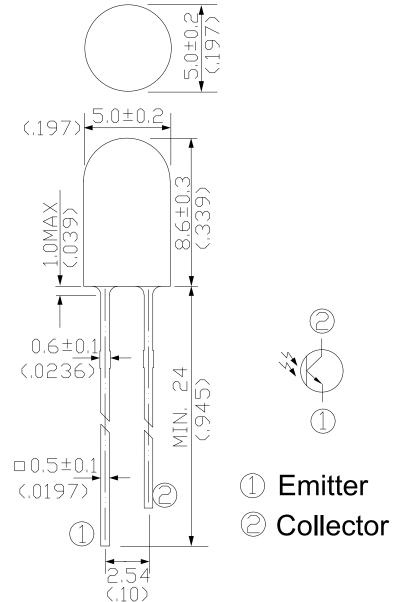


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### **Package Dimensions**



Note: 1. All dimensions are in millimeters(inches) 2. Tolerances unless dimensions ± 0.25mm(.01")

Parameter	Symbol	Rating	Units				
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V				
Emitter-Collector-Voltage	V <sub>ECO</sub>	6.5	V				
Collector Current	Ic	20	mA				
Lead Soldering Temperature	Tsol	260	Ĉ				
Operating Temperature	Topr	-20~+85	Ĉ				
Storage Temperature	Tstg	-40~+85	Ĉ				

#### Absolute Maximum Ratings (Ta=25°C)

Notes: \*1:Soldering time  $\leq$  5 seconds.

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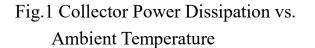
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Electro-Optical Characteristics (Ta=25°C)								
Parameter	Symbol	Min.	Тур.	Max.	Units	Condition		
Range of Spectral Bandwidth	λ0.5	840		1100	nm			
Wavelength of	λ <sub>P</sub>		940		nm			
Peak Sensitivity								
Collector – Emitter	BVCEO	30			V	Ic=100µA, Ib=0		
Breakdown Voltage								
Emitter-Collector	BV <sub>ECO</sub>	6.5			v	Ic=100µA, Ib=0		
Breakdown Voltage								
Collector Dark Current	I <sub>CEO</sub>			100	nA	$V_{CE}=20V$ ,		
						H=0mw/cm2		
Collector-Emitter	VCE (S)	-		0.2	V	Ic=2mA,		
Saturation Voltage						I <sub>B</sub> =100μA		
On State Collector	I <sub>C (on)</sub>	0.7	3.0		mA	Ee=1mW/cm2,		
Current						V <sub>CE</sub> =5V		
DC Current Amplification Factor	H <sub>FE</sub>	1000		1800		$V_{CE}$ =5V, IC=2mA		
Rise/Fall Time	t <sub>r</sub> /t <sub>f</sub>		15/15		μS	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA		
					.	$R_L=1000\Omega$		

### ■ Electro-Optical Characteristics (Ta=25°C)

### Typical Electro-Optical Characteristics Curves



Relative Spectral Sensitivity(%) Collector Power Dissipation (mW) Ta=25° -40 -20 **Ambient Temperature Ta(°C)** Wavelength(nm)

Fig.2 Spectral Sensitivity

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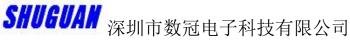


Fig.3 Relative Collector Current vs.

## Ambient Temperature 160 Vce=5V Relative Collector Current (%) 140 $Ee=1 \, mW/cm^2$ 120 100 80 60 40 20

Fig.5 Collector Dark Current vs.

Ambient Temperature

20

10

30

40

Ambient Temperature Ta(°C)

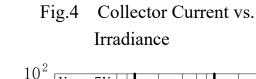
60

50

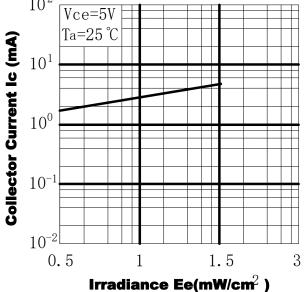
70 80

0

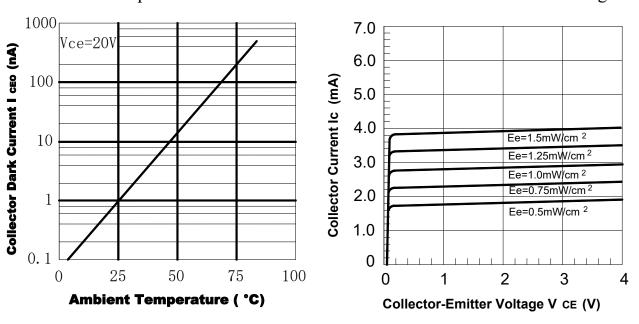
0



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### Collector Current vs. Fig.6 Collector-Emitter Voltage



#### **Packing Quantity Specification**

1000 PCS/1 Bag 1.

#### Notes

Above specification may be changed without notice. SHUGUAN will reserve authority on 1. SHENZHEN SHUGUAN ELECTRONIC TECHNOLOGY CO., LTD. V1.0 2011.03.05

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material change for above specification.

- 2. Before using this product, be sure to test it. The use and storage conditions must not exceed the limit parameters specified in this manual. The company will not be responsible for any damage to the product caused by the use of the product beyond the limit parameters.
- 3. Stored at a temperature not higher than 30° C and humidity not higher than 60%RH, the product shelf life is 6 months. Keeping the product in an airtight container with a desiccant can extend the shelf life of the product to some extent. Poor storage conditions can cause corrosion of product leads or changes in product performance.
- 4. After opening, the product must be used within 168 hours (recommended working environment temperature not higher than 30 °C, humidity not higher than 60%). If it is not used up, the remaining material must be stored in an environment where the temperature is not higher than 30° C and the humidity is not higher than 10%.
- 5. For products that have not been soldered, if the hygroscopic agent or packaging fails, or the product does not meet the above valid storage conditions, baking can play a certain performance recovery effect. Baking conditions:  $65 \pm 5^{\circ}$ C, duration 96H.
- 6. Static electricity and surges will cause changes in product characteristics, such as forward voltage reduction, etc. If the situation is serious, it will even damage the product, so effective anti-static measures must be taken during use. All related equipment and machines should be properly grounded, and other measures against static electricity and surges must be taken. The use of anti-static wristbands, anti-static mats, anti-static work clothes, work shoes, gloves, and anti-static containers are all effective measures to prevent static electricity and surges.
- 7. Shaping of the pins must be done before soldering. When shaping, the bending position of the lead must be at least 3mm from the bottom of the encapsulation resin, while avoiding bending the same position multiple times.
- 8. Use a suitable tool to hold the pins in place while shaping to avoid stressing the resin. In particular, the connection part between the pin and the resin cannot be used as a fulcrum. The stress generated in this way will directly damage the light-emitting structure inside the product, resulting in changes in product characteristics or even damage.
- 9. When assembling the product, the distance between the solder holes on the PCB must be strictly matched with the pin spacing of the product.
- 10. Welding should pay special attention to:

(1) Manual soldering: the tip temperature of the soldering iron (up to 30W) should not exceed  $350^{\circ}$  C; the soldering iron must be grounded, and the static electricity should not exceed the range; the soldering time should not exceed 3 seconds; the soldering position should be at least 3 mm away from the colloid.

(2) Dip soldering: the maximum temperature for dip soldering is  $260^{\circ}$  C; the dip soldering time does not exceed 5 seconds; the dip soldering position is at least 3 mm away from the colloid.